

MATERIALS SCIENCEDOI <https://doi.org/10.30525/978-9934-26-264-7-10>**STRUCTURE EVOLUTION
IN AL₇₀SI₂₀NI₁₀ RAPIDLY-QUENCHED ALLOY****ЕВОЛЮЦІЯ СТРУКТУРИ
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Al-Si-Ni alloys are used in such industrial areas as automotive, aerospace, electronics, etc. With the aim of utilizing a high-strength material with light weight a great effort has been devoted to the production of amorphous Al-rich alloys. It is considered, that rapidly solidified Al–Ni–Si amorphous alloys are a better choice for practical application as materials with high strength, low density, and useful physical properties [1]. It is known the physical properties of a material at an amorphous or nanocrystalline state depend on its structure and phase composition. Controlled change of structure

allows obtaining the desired properties of a material. So the investigation of the structure evolution of rapidly-quenched $\text{Al}_{70}\text{Ni}_{10}\text{Si}_{20}$ alloy is presented in this study.

The $\text{Al}_{70}\text{Ni}_{10}\text{Si}_{20}$ alloy was produced by rapid cooling from a melt in the form of a ribbon using the melt-spinning technique. Thickness of the ribbon was about 25 μm and width about 1 cm. The DTA-method was used for alloy investigation under continuous heating. The heating was performed using synchronous thermal analyzer Linseis STA PT 1600 under argon atmosphere at the heating rate of 6 K/min and temperature interval from 293 – 673 K. Isothermal annealing at different exposures and temperatures was used to induce the structure evolution. After annealing the structure changes were investigated using back-scattered X-ray diffraction (XRD) method ($\text{Cu-K}\alpha$).

The result of DTA of $\text{Al}_{70}\text{Ni}_{10}\text{Si}_{20}$ alloy (Fig. 1) shows three exothermic peaks on the DTA curve: the first peak in the temperature interval of 389 – 406 K; the second one in the temperature interval of 491 – 522 K; and the third one in the temperature interval of 530 – 546 K. The crystallization onset temperature (T_x) was obtained as 389.6 K. Three exothermic peaks may indicate the structure evolution occurs through three-stages and matches the multi-stage model [2, 3].

As-quenched $\text{Al}_{70}\text{Si}_{20}\text{Ni}_{10}$ alloy was investigated using the XRD method and the corresponding curve is presented in Fig. 2 marked 'as-q'. The curve is characterized by a wide halo with small peaks of reflexes and represents an amorphous-nanocrystalline structure. Compared with the similar Al-Si-Ni alloy studied in [4] it can be mentioned that $\text{Al}_{65}\text{Si}_{25}\text{Ni}_{10}$ was obtained in an amorphous state, while $\text{Al}_{70}\text{Si}_{20}\text{Ni}_{10}$ alloy includes some nanocrystalline metastable hexagonal H-phase [5]. However, DTA curves of these alloys are quite similar and represent the process of alloy crystallization.

The samples of the investigated alloy, isothermally annealed at temperatures up to 533 K and exposures up to 1 hour, was studied using the XRD method. The X-ray intensity curves of the alloy annealed at the temperature of 348 K during up to 60 minutes are shown in Fig. 2. This temperature is lower than the crystallization onset temperature (T_x) defined by the DTA (393.6 K). Nevertheless, clear narrow peaks are seen on the intensity curves indicating the H-phase content increasing in an amorphous matrix of the alloy. So, the H-phase was formed in a minor quantity at quenching process and continued to growth in the annealing at 348 K accompanying by the amorphous phase disintegration.

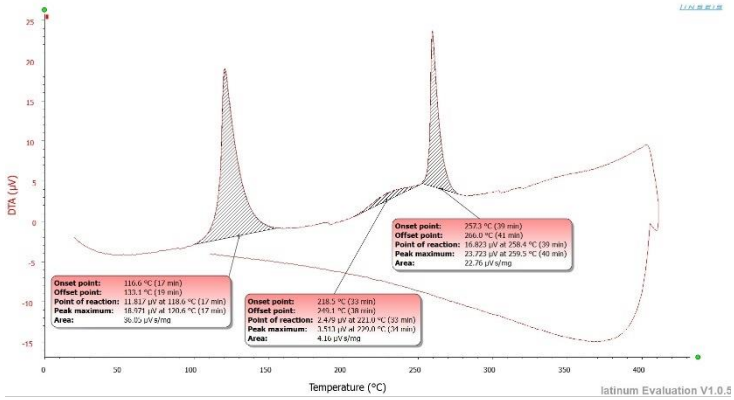


Fig. 1. DTA of the rapidly-quenched $\text{Al}_{70}\text{Si}_{20}\text{Ni}_{10}$ alloy

The hexagonal H-phase was also observed after annealing at 403 K and 463 K (Fig. 3). Its formation can be assigned to the first crystallization peak on the DTA curve.

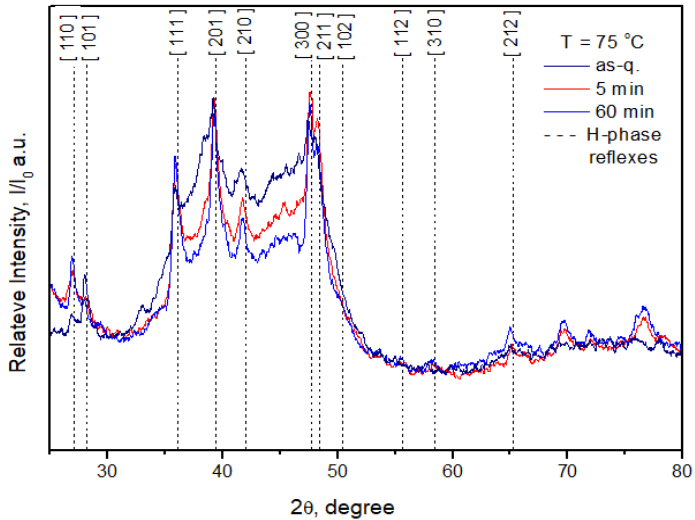


Fig. 2. X-ray intensity curves of the $\text{Al}_{70}\text{Si}_{20}\text{Ni}_{101}$ alloy annealed at 348 K

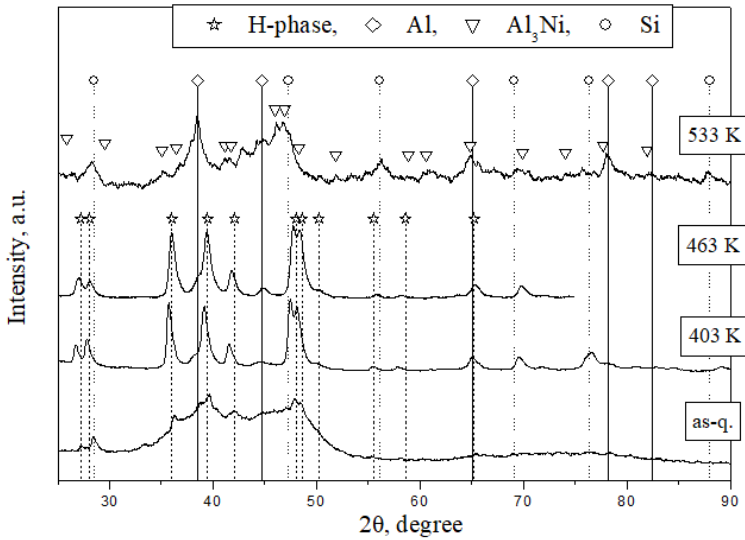


Fig. 3. X-ray intensity curves of $\text{Al}_{70}\text{Si}_{20}\text{Ni}_{10}$ alloy annealed during 1 hour

The intensity curves that correspond to the annealing temperature of 403 K and 463 K are almost similar; the difference is only in peaks intensities. This indicates the H-phase content increased at higher temperature annealing. The H-phase was not observed after annealing at the temperature of 533 K that indicates the H-phase decomposition. Instead, a nanocrystalline phases Al, Si, and Al_3Ni were observed after annealing at this temperature. The temperature of 533 K is close to the third exothermic peak on the DTA curve. Therefore we assume that the third exothermic peak corresponds to the formation of the Al_3Ni intermetallic. From the obtained results, it can be assumed that the second small exothermic peak detected in the temperature range of 491 – 522K is caused by the formation of Al and Si phases.

The heating-induced structure evolution of $\text{Al}_{70}\text{Ni}_{10}\text{Si}_{20}$ rapidly-quenched alloy was studied by means of DTA and XRD methods. The first exothermic DTA peak was obtained at $T_x = 389.6$ K. The crystallization process is accompanied by the formation of an intermediate metastable hexagonal H-phase. It was shown that the H-phase is stable within the temperature interval of about 403-463 K and at time duration of at least 1 hour. Based on the DTA results, the crystallization temperature of this alloy is 389.6 K, which could be considered as the temperature limit of stability, but as XRD results

showed, 1-hour annealing at about 340 K causes partial nanocrystallization. So, the amorphous phase in the $\text{Al}_{70}\text{Ni}_{10}\text{Si}_{20}$ alloy is very unstable

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